

On new page 35 following the claims, please insert the following:

**COMPLEX OXIDES FOR USE IN SEMICONDUCTOR DEVICES AND RELATED
METHODS**

Abstract of the Disclosure

A semiconductor device includes a semiconductor substrate, a first oxide layer on the semiconductor substrate including an element from the semiconductor substrate, and a second oxide layer on the first oxide layer opposite the semiconductor substrate. The second oxide layer includes a stoichiometric, single-phase complex oxide represented by the formula:



in which the elemental oxide components, (A_mO_n) and (B_qO_r) are combined so that $h = j$ or, equivalently, $ma = bq$, and a, b, h, j, k, m, n, q and r are non-zero integers; and

wherein:

A is an element of the lanthanide rare earth elements of the periodic table or the trivalent elements from cerium to lutetium; and

B is an element of the transition metal elements of groups IIIB, IVB or VB of the periodic table.